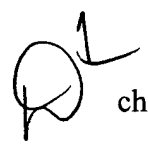


CLAIM AMENDMENTS

Claims 1-10 (canceled).

 Claim 11 (currently amended): A method for removing a deposited film inside a chamber which comprises:

- providing a hot element in the chamber, said hot element disposed away from the deposited film, the hot element having at least a surface which comprises platinum;
- exhausting said chamber;
- heating the hot element to 400° C. or higher;
- supplying ~~a cleaning gas~~ into the chamber a cleaning gas containing at least one halogen atom;
- contacting the cleaning gas with the heated hot element to decompose and/or activate the cleaning gas and generate an activated species therefrom;
- allowing the activated species to convert the deposited film into a gaseous substance; and
- removing the gaseous substance from the chamber.

Claim 12 (previously added): The method according to claim 11, wherein said chamber comprises a CVD apparatus and the method further comprises:

- heating the hot element;
- supplying a material gas to the chamber;
- contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and
- forming the deposited film which comprises at least one element from said material gas on a substrate.

Claim 13 (previously added): The method according to claim 11, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.

Claim 14 (previously added): The method according to claim 12, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.

Claim 15 (previously added): The method according to claim 11, wherein said cleaning gas is a gas containing at least one of fluorine (F<sub>2</sub>), chlorine (Cl<sub>2</sub>), nitrogen trifluoride (NF<sub>3</sub>), carbon tetrafluoride (CF<sub>4</sub>), hexafluoroethane (C<sub>2</sub>F<sub>6</sub>), octafluoropropane (C<sub>3</sub>F<sub>8</sub>), carbon tetrachloride (CCl<sub>4</sub>), pentafluorochloroethane (C<sub>2</sub>ClF<sub>5</sub>), trifluorochlorine (ClF<sub>3</sub>), trifluorochloromethane (CClF<sub>3</sub>), and sulfur hexafluoride (SF<sub>6</sub>), and mixtures thereof.

Claim 16 (previously added): The method according to claim 12, wherein said cleaning gas is a gas containing at least one of fluorine (F<sub>2</sub>), chlorine (Cl<sub>2</sub>), nitrogen trifluoride (NF<sub>3</sub>), carbon tetrafluoride (CF<sub>4</sub>), hexafluoroethane (C<sub>2</sub>F<sub>6</sub>), octafluoropropane (C<sub>3</sub>F<sub>8</sub>), carbon tetrachloride (CCl<sub>4</sub>), pentafluorochloroethane (C<sub>2</sub>ClF<sub>5</sub>), trifluorochlorine (ClF<sub>3</sub>), trifluorochloromethane (CClF<sub>3</sub>), sulfur hexafluoride (SF<sub>6</sub>), and mixtures thereof.

*1*  
*cont*  
Claims 17-20 (~~withdrawn~~) *canceled by "B"*

Claims 21-26 (canceled)

Claim 27 (currently amended): A method for removing a deposited film from a wall inside a chamber, said method comprising:

providing a hot element, said hot element disposed away from said wall and said deposited film, said hot element having at least a surface which is composed of platinum;

heating said hot element to 400° C. or higher;

supplying said chamber with a cleaning gas containing at least one halogen atom, and first contacting said hot element with said gas to thereby activate said gas;

thereafter contacting the deposited film with said activated cleaning gas and converting said deposited film into a gaseous substance; and

removing said gaseous substance from said chamber.

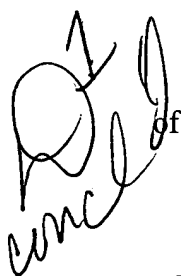
Claim 28 (previously added): The method according to claim 27, wherein said chamber comprises a CVD apparatus and the method further comprises:

heating the hot element;

supplying a material gas to the chamber;

contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and

forming the deposited film which comprises at least one element from said material gas on a substrate.



Claim 29 (previously added): The method according to claim 27, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.

Claim 30 (previously added): The method according to claim 28, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.

Claim 31 (previously added): The method according to claim 27, wherein said cleaning gas is a gas containing at least one of fluorine (F<sub>2</sub>), chlorine (Cl<sub>2</sub>), nitrogen trifluoride (NF<sub>3</sub>), carbon tetrafluoride (CF<sub>4</sub>), hexafluoroethane (C<sub>2</sub>F<sub>6</sub>), octafluoropropane (C<sub>3</sub>F<sub>8</sub>), carbon tetrachloride (CCl<sub>4</sub>), pentafluorochloroethane (C<sub>2</sub>ClF<sub>5</sub>), trifluorochlorine (ClF<sub>3</sub>), trifluorochloromethane (CClF<sub>3</sub>), and sulfur hexafluoride (SF<sub>6</sub>), and mixtures thereof.

Claim 32 (previously added): The method according to claim 28, wherein said cleaning gas is a gas containing at least one of fluorine (F<sub>2</sub>), chlorine (Cl<sub>2</sub>), nitrogen trifluoride (NF<sub>3</sub>), carbon tetrafluoride (CF<sub>4</sub>), hexafluoroethane (C<sub>2</sub>F<sub>6</sub>), octafluoropropane (C<sub>3</sub>F<sub>8</sub>), carbon tetrachloride (CCl<sub>4</sub>), pentafluorochloroethane (C<sub>2</sub>ClF<sub>5</sub>), trifluorochlorine (ClF<sub>3</sub>), trifluorochloromethane (CClF<sub>3</sub>), sulfur hexafluoride (SF<sub>6</sub>), and mixtures thereof.